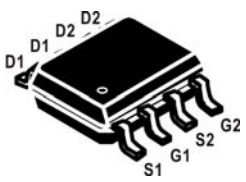
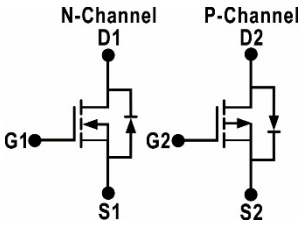
SGD60C01S

60V / -60V Complementary, Power MOSFET

N-Channel :	P-Channel :	SOP-8	N-Channel / P-Channel
V_{DSS} , 60V $R_{DS(ON)}$, 45mΩ (max.) @ V_{GS}=10V $R_{DS(ON)}$, 50mΩ (max.) @ V_{GS}=4.5V I_D , 7.9A	V_{DSS} , -60V $R_{DS(ON)}$, 83mΩ (max.) @ V_{GS}=-10V $R_{DS(ON)}$, 106mΩ (max.) @ V_{GS}=-4.5V I_D , -5.9A		

Description

The SGD60C01S uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge.

The complementary Power MOSFETs may be used in H-bridge, Inverters and other applications.

Features

- Low On-Resistance
- Low Input Capacitance
- Low Miller Charge
- Low Input/Output Leakage
- Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGD60C01S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Value		Unit
Drain-Source Voltage		V_{DS}	60	-60	V
Gate-Source Voltage		V_{GS}	±20		V
Drain Current-Continuous	T_A=25°C	I_D	7.9	-5.9	A
	T_A=100°C		5.9	-4.6	A
Drain Current-Pulsed Note 1		I_{DM}	15	-11.5	A
Maximum Power Dissipation	T_A=25°C	P_D	3.5		W
Operating Junction Temperature Range		T_J T_{STG}	-55 to +150		°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Maximum Junction-to-Ambient Note 2	$R_{\theta JA}$	t<10 sec.	-	-	85	°C/W
Maximum Junction-to-Case Note 2	$R_{\theta JC}$	Steady State	-	-	36	°C/W

N-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_{DS}=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V	-	-	1	μA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_{DS}=250μA	1	-	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_{DS}=4A	-	-	45	mΩ
		V_{GS}=4.5V, I_{DS}=3A	-	-	50	

DYNAMIC CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Input Capacitance	C_{iss}	V_{DS}=15V, V_{GS}=0V, f=1MHz	-	1027	-	pF
Output Capacitance	C_{oss}		-	65	-	
Reverse Transfer Capacitance	C_{rss}		-	46	-	

SWITCHING CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=30V, V_{GS}=10V, R_G=3.3Ω, I_D=4A	-	3	-	ns
Rise Time	t_r		-	34	-	
Turn-Off Delay Time	$T_{d(off)}$		-	23	-	
Fall Time	t_f		-	6	-	
Total Gate Charge at 4.5V	Q_g	V_{DS}=48V, I_{DS}=4A, V_{GS}=10V	-	19	-	nC
Gate to Source Gate Charge	Q_{gs}		-	2.6	-	
Gate to Drain “Miller” Charge	Q_{gd}		-	4.1	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=1A	-	-	1.2	V
Continuous Source Current	I_S	V_G=V_D=0V, Force Current	-	-	4.7	A
Pulsed Source Current	I_{SM}		-	-	20	A

Notes:

1. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 in still air.

P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_{DS}=-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V, V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_{DS}=-250μA	-1	-	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_{DS}=-5A	-	-	83	mΩ
		V_{GS}=-4.5V, I_{DS}=-2A	-	-	106	

DYNAMIC CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Input Capacitance	C_{iss}	V_{DS}=-15V, V_{GS}=0V, f=1MHz	-	1447	-	pF
Output Capacitance	C_{oss}		-	97.3	-	
Reverse Transfer Capacitance	C_{rss}		-	70	-	

SWITCHING CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=-30V, V_{GS}=-10V, R_G=3.3Ω, I_D=-5A	-	9.6	-	ns
Rise Time	t_r		-	18	-	
Turn-Off Delay Time	$T_{d(off)}$		-	45.8	-	
Fall Time	t_f		-	45.8	-	
Total Gate Charge at -4.5V	Q_g	V_{DS}=-48V, I_{DS}=-5A, V_{GS}=-4.5V	-	9.86	-	nC
Gate to Source Gate Charge	Q_{gs}		-	3.08	-	
Gate to Drain “Miller” Charge	Q_{gd}		-	2.95	-	

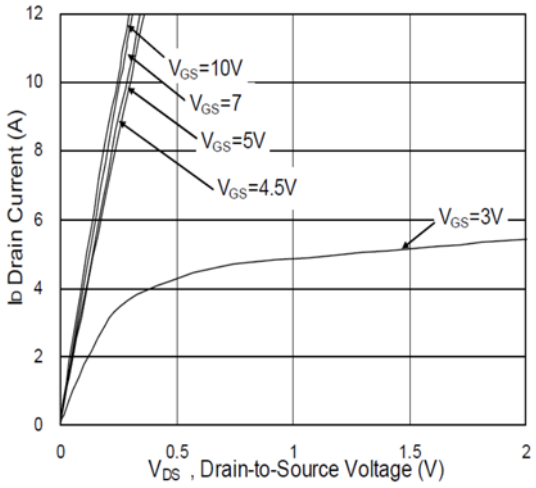
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-1A	-	-	-1.2	V
Continuous Source Current	I_S	V_G=V_D=0V, Force Current	-	-	-5.9	A
Pulsed Source Current	I_{SM}		-	-	-13	A

Notes:

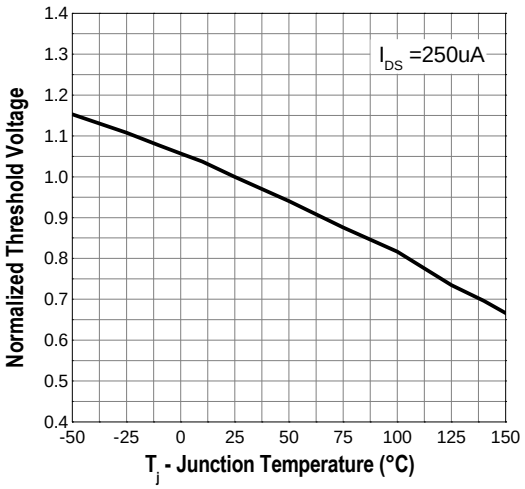
1. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 in still air.

N-Channel Typical Operating Characteristics

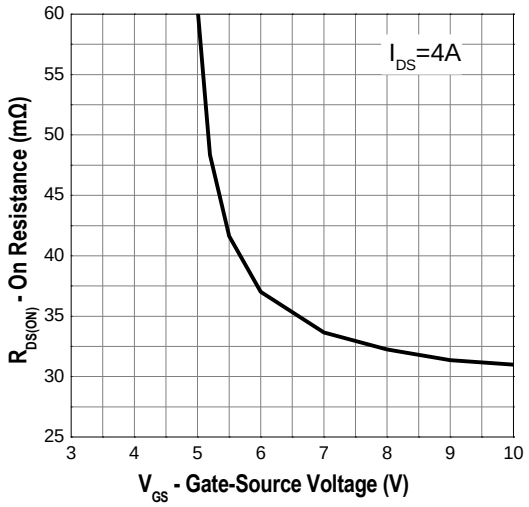
Output Characteristics



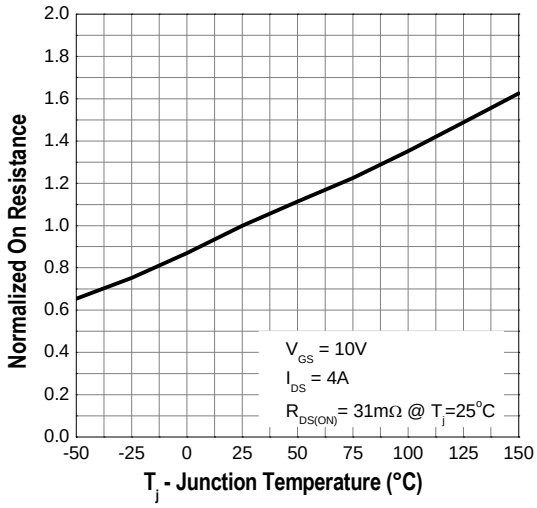
Gate Threshold Voltage



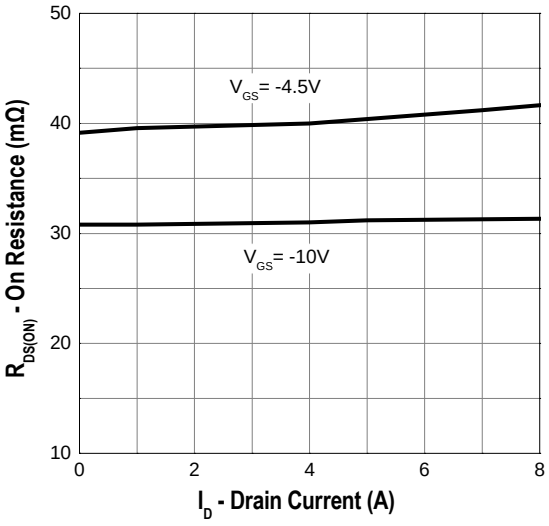
Gate-Source On Resistance



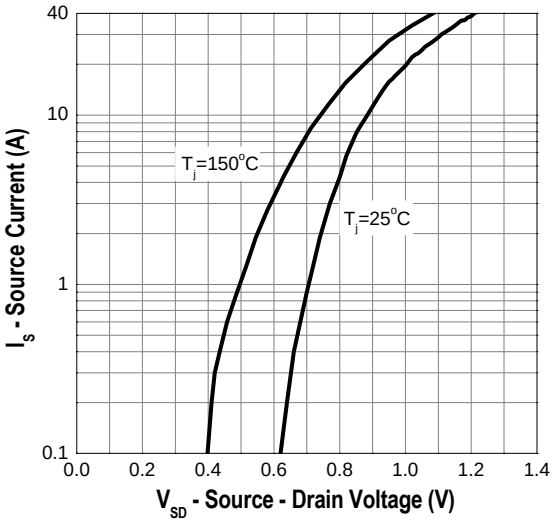
Drain-Source On Resistance



Drain-Source On Resistance

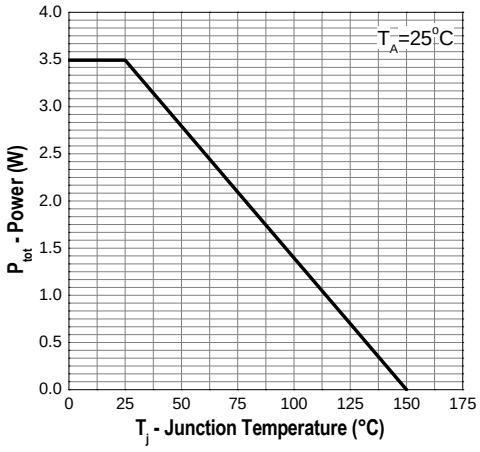


Source-Drain Diode Forward

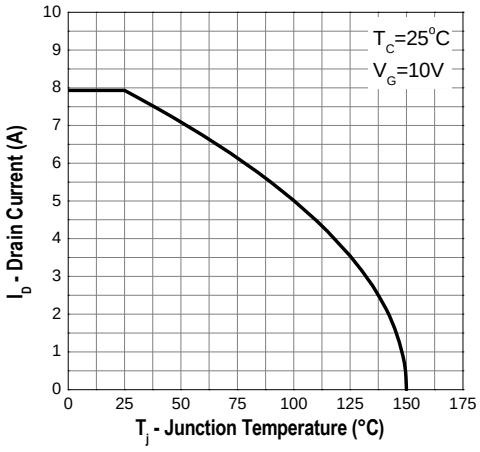


N-Channel Typical Operating Characteristics (Cont.)

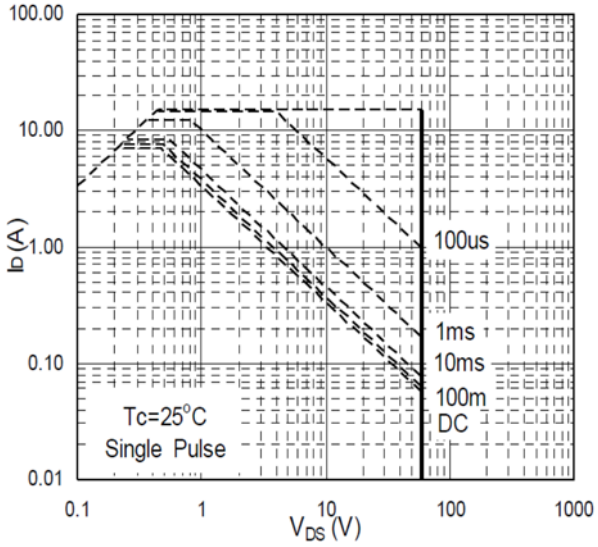
Power Dissipation



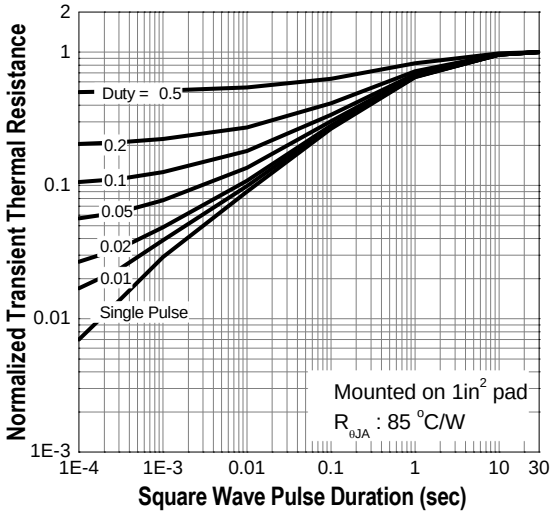
Drain Current



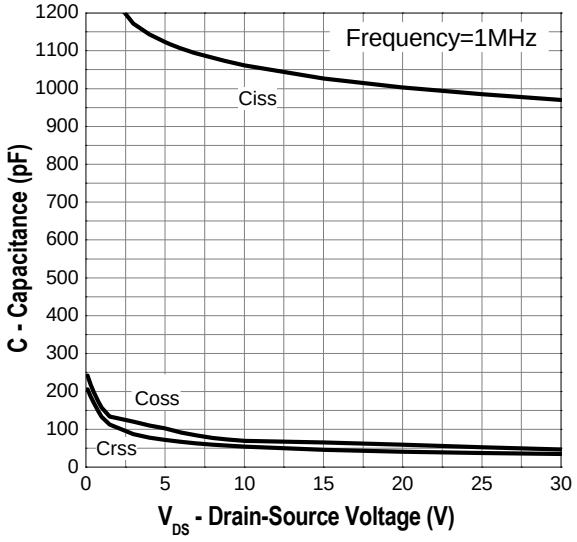
Safe Operation Area



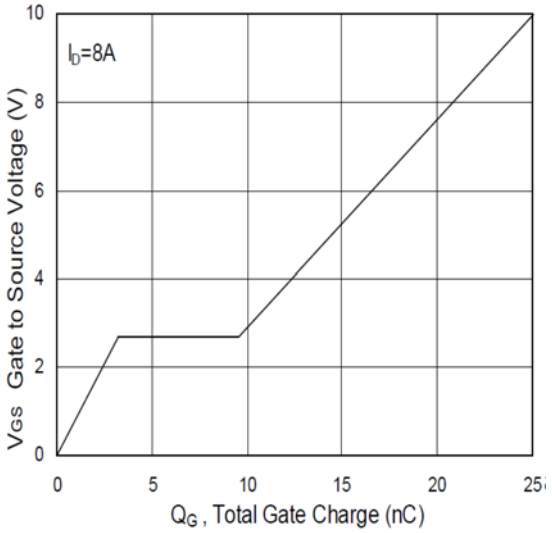
Thermal Transient Impedance



Capacitance

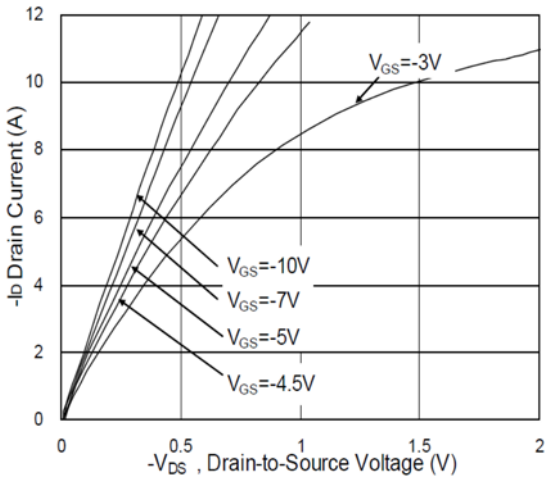


Gate Charge

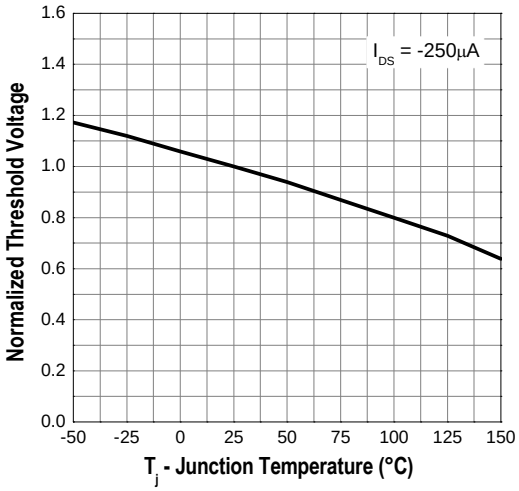


P-Channel Typical Operating Characteristics

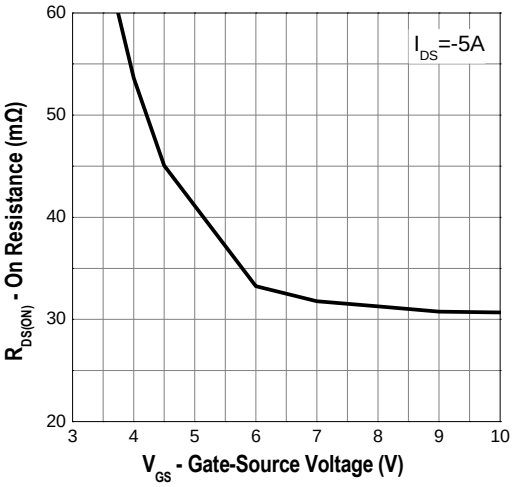
Output Characteristics



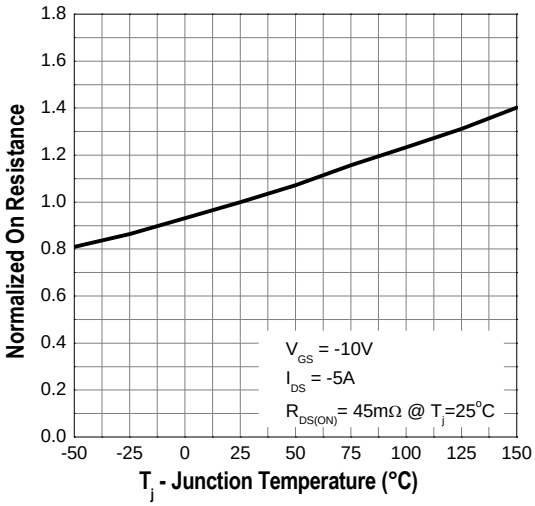
Gate Threshold Voltage



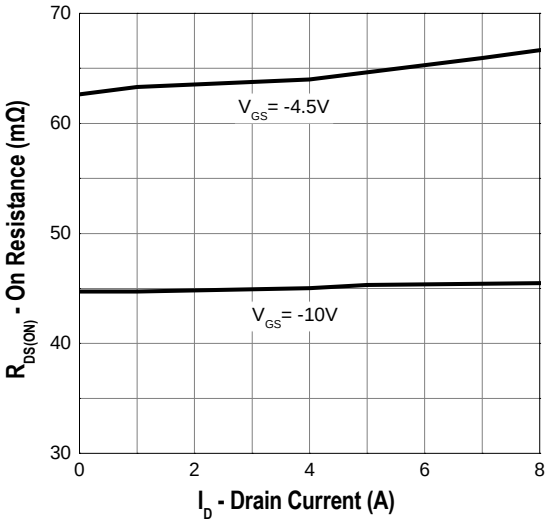
Gate-Source On Resistance



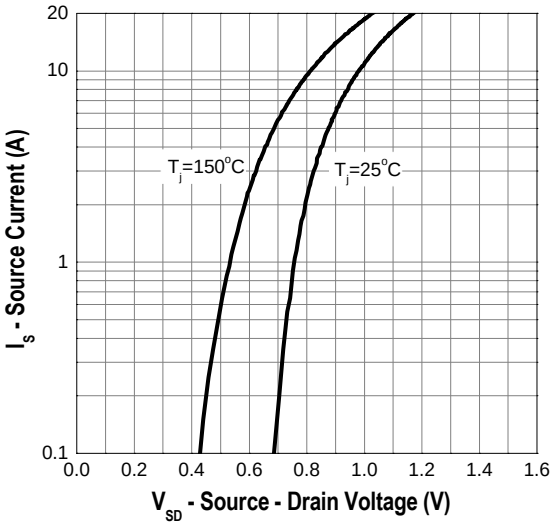
Drain-Source On Resistance



Drain-Source On Resistance

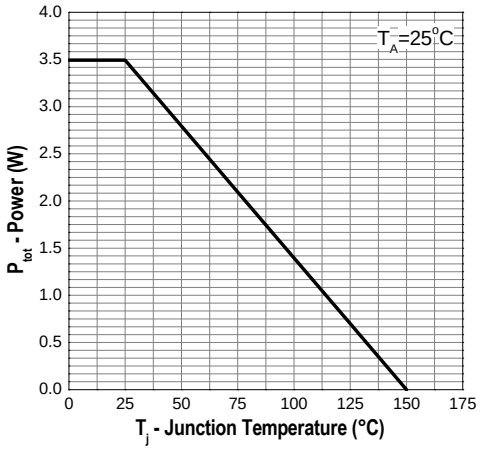


Source-Drain Diode Forward

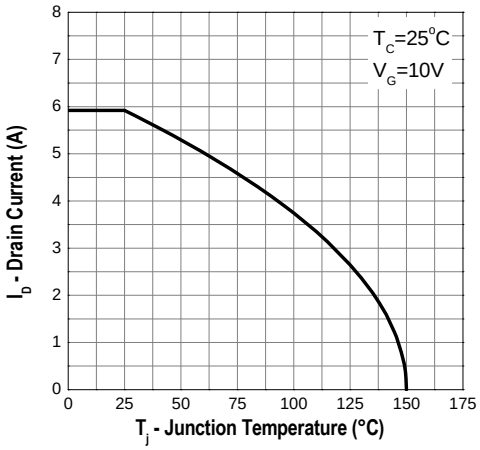


P-Channel Typical Operating Characteristics (Cont.)

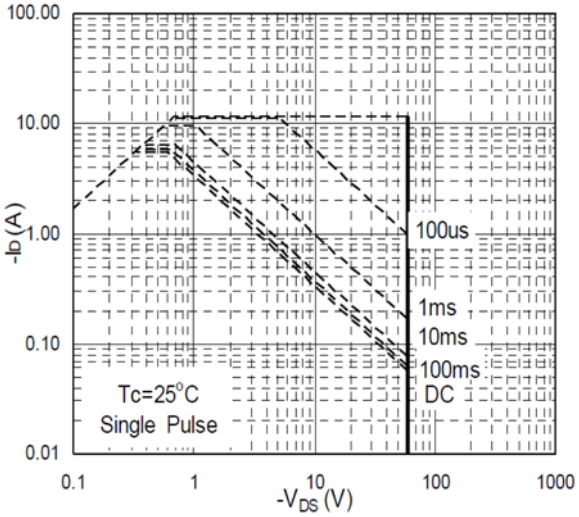
Power Dissipation



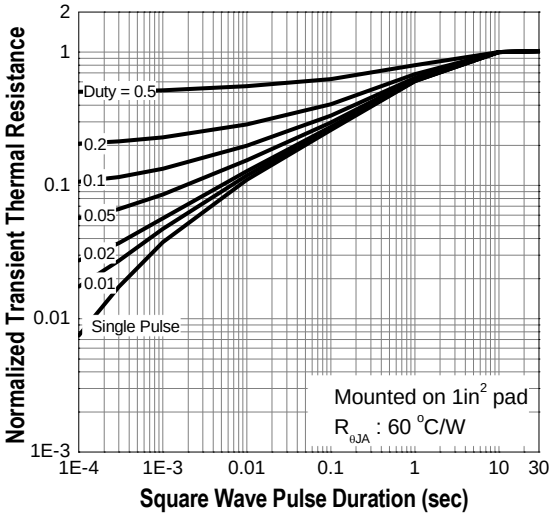
Drain Current



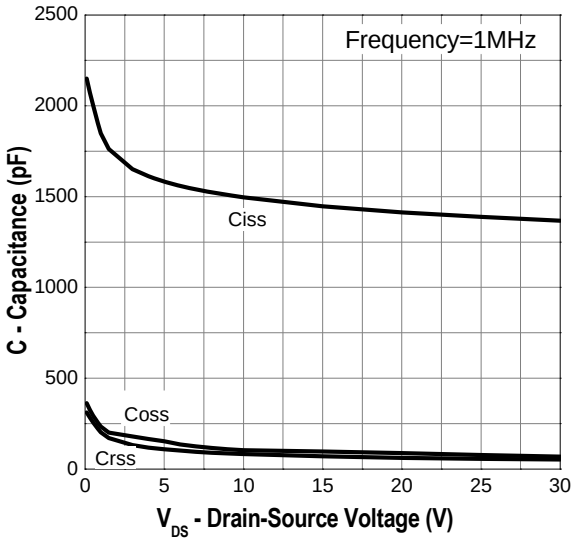
Safe Operation Area



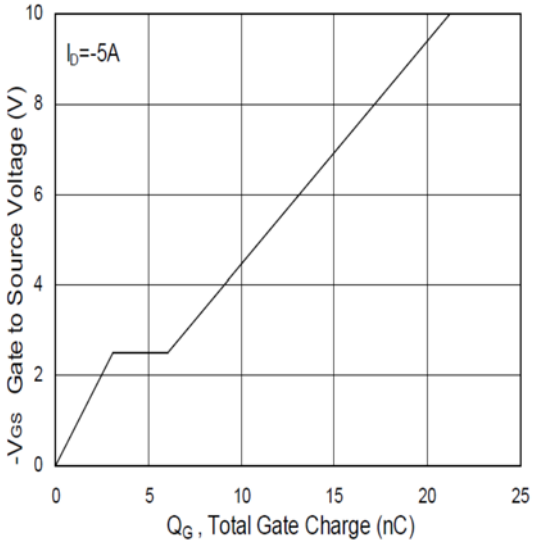
Thermal Transient Impedance



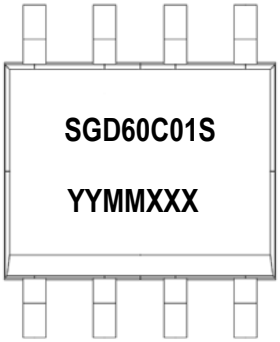
Capacitance



Gate Charge

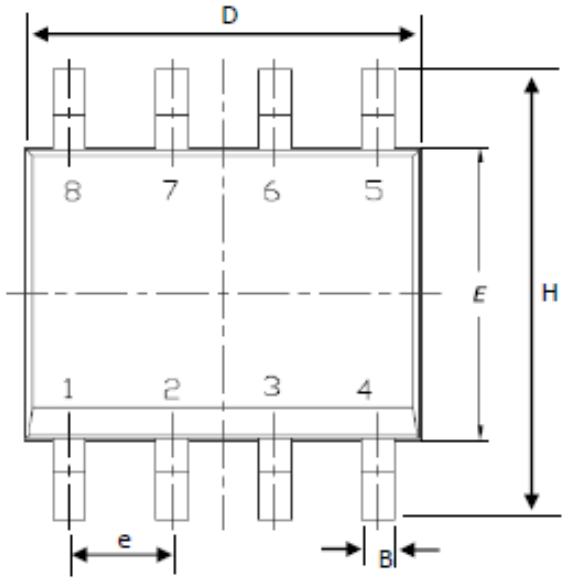


Marking Information

SOP-8 (S)	Marking Rule
Laser Marking  Diagram	Line 1：Device Name SGD60C01S Line 2：Date Code YYMMXXX YY：Year Code MM：Month Code XXX：Serial Number

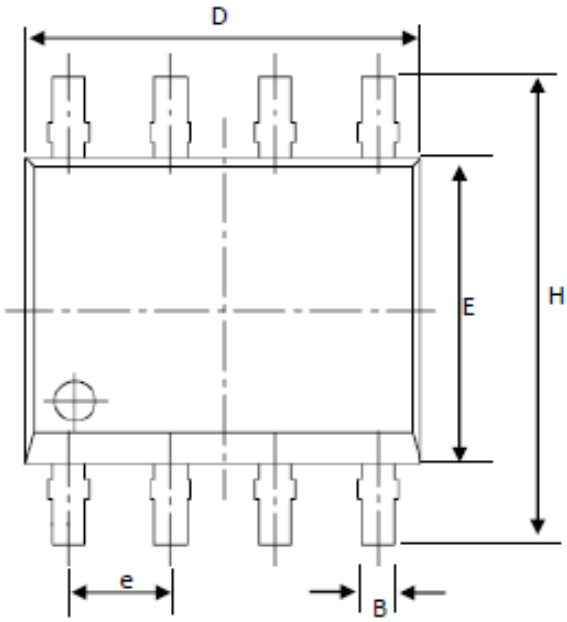
Package of Dimension

G-TYPE



Symbol	Min	Nor	Max
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
B	0.31	0.41	0.51
c	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
H	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00

B-TYPE

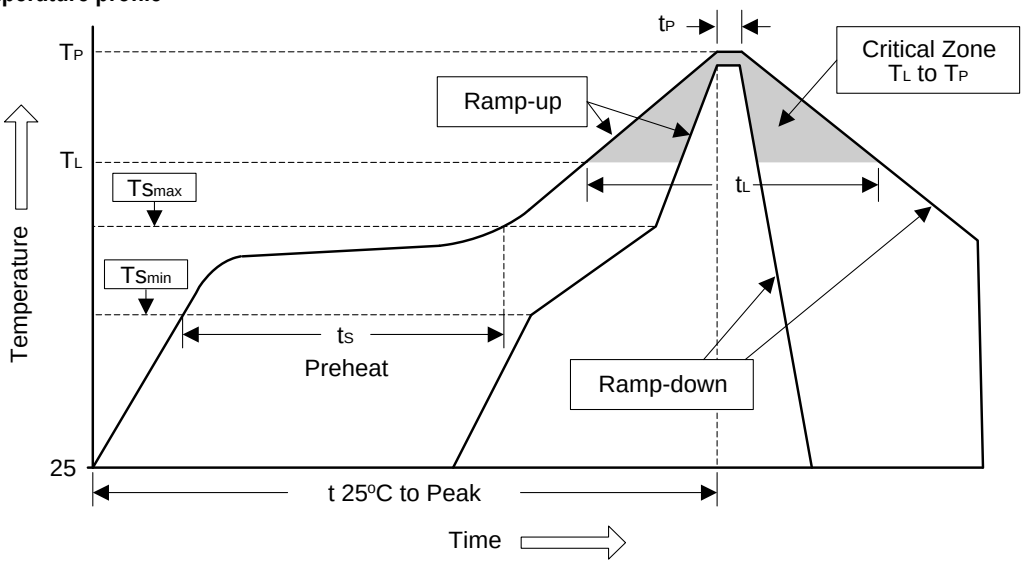


1. All dimension are in millimeters.
2. Dimension does not include burrs and mold flash/protrusions.

Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat - Temperature Min (Ts_{min}) - Temperature Max (Ts_{max}) - Time (min to max) (ts)	 100°C 150°C 60 to 120 sec	 150°C 200°C 60 to 180 sec
Tsmax to T_L - Ramp-up Rate	 <3°C/sec	 <3°C/sec
Time maintained above: - Temperature (T_L) - Time (t_L)	 183°C 60 to 150 sec	 217°C 60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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